

# Monica De Seta

## List of Publications by Year in descending order

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Version: 2024-02-01

20  
papers

279  
citations

759233

12  
h-index

888059

17  
g-index

20  
all docs

20  
docs citations

20  
times ranked

300  
citing authors

#	ARTICLE	IF	CITATIONS
1	Room temperature operation of <i>n</i> -type Ge/SiGe terahertz quantum cascade lasers predicted by non-equilibrium Green's functions. Applied Physics Letters, 2019, 114, .	3.3	45
2	Long intersubband relaxation times in <i>n</i> -type germanium quantum wells. Applied Physics Letters, 2011, 99, .	3.3	26
3	Physical mechanisms of intersubband-absorption linewidth broadening in $n$ -type Ge/SiGe quantum wells. Physical Review B, 2014, 90, .	3.2	25
4	Reduction of threading dislocation density beyond the saturation limit by optimized reverse grading. Physical Review Materials, 2020, 4, .	2.4	20
5	On-chip infrared photonics with Si-Ge-heterostructures: What is next?. APL Photonics, 2022, 7, .	5.7	18
6	Electron Dynamics in Silicon-Germanium Terahertz Quantum Fountain Structures. ACS Photonics, 2016, 3, 403-414.	6.6	17
7	THz intersubband electroluminescence from <i>n</i> -type Ge/SiGe quantum cascade structures. Applied Physics Letters, 2021, 118, .	3.3	15
8	X-ray diffraction study of plastic relaxation in Ge-rich SiGe virtual substrates. Physical Review B, 2012, 85, .	3.2	14
9	Combined effect of electron and lattice temperatures on the long intersubband relaxation times of Ge/Si <sub>x</sub> Ge <sub>1-x</sub> quantum wells. Physical Review B, 2014, 89, .	3.2	14
10	Onset of plastic relaxation in the growth of Ge on Si(001) at low temperatures: Atomic-scale microscopy and dislocation modeling. Physical Review B, 2013, 88, .	3.2	13
11	Second Harmonic Generation in Germanium Quantum Wells for Nonlinear Silicon Photonics. ACS Photonics, 2021, 8, 3573-3582.	6.6	13
12	Terahertz absorption-saturation and emission from electron-doped germanium quantum wells. Optics Express, 2020, 28, 7245.	3.4	12
13	Intersubband Transition Engineering in the Conduction Band of Asymmetric Coupled Ge/SiGe Quantum Wells. Crystals, 2020, 10, 179.	2.2	11
14	Determination of the free carrier concentration in atomic-layer doped germanium thin films by infrared spectroscopy. Journal of Optics (United Kingdom), 2014, 16, 094010.	2.2	8
15	THz intersubband absorption in <i>n</i> -type Si <sub>1-x</sub> Ge <sub>x</sub> parabolic quantum wells. Applied Physics Letters, 2021, 118, .	3.3	8
16	Submicron Size Schottky Junctions on As-Grown Monolayer Epitaxial Graphene on Ge(100): A Low-Invasive Scanned-Probe-Based Study. ACS Applied Materials & Interfaces, 2019, 11, 35079-35087.	8.0	7
17	Electron Population Dynamics in Optically Pumped Asymmetric Coupled Ge/SiGe Quantum Wells: Experiment and Models. Photonics, 2020, 7, 2.	2.0	5
18	Disentangling elastic and inelastic scattering pathways in the intersubband electron dynamics of <i>n</i> -type Ge/SiGe quantum fountains. Physical Review B, 2020, 101, .	3.2	4

#	ARTICLE	IF	CITATIONS
19	Tuning the Doping of Epitaxial Graphene on a Conventional Semiconductor via Substrate Surface Reconstruction. <i>Journal of Physical Chemistry Letters</i> , 2021, 12, 1262-1267.	4.6	4
20	Terahertz intersubband electroluminescence from n-type germanium quantum wells. , 2021, , .		0